



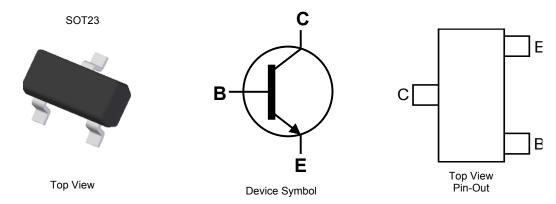
#### **40V NPN SMALL SIGNAL TRANSISTOR IN SOT23**

#### **Features**

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type: MMBT4403
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

#### **Mechanical Data**

- Case: SOT23
- Case material: molded Plastic "Green" Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)



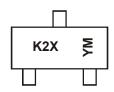
#### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT4401-7-F	AEC-Q101	K2X	7	8	3,000
MMBT4401-13-F	AEC-Q101	K2X	13	8	10,000
MMBT4401Q-13-F	Automotive	K2X	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



K2X = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: A = 2013)

M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Kev

Year	2010	20	)11	2012	2	2013	2014		2015	2016		2017
Code	Х		Υ	Z		Α	В		С	D		Е
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



### Absolute Maximum Ratings (@TA = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	600	mA
Peak Collector Current	I <sub>CM</sub>	1	Α
Peak Base Current	I <sub>BM</sub>	200	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	D	310	mW
Power Dissipation	(Note 7)	P <sub>D</sub>	350	IIIVV
Thermal Resistance, Junction to Ambient	(Note 6)	В	403	°C/M
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	357	°C/W
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	350	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C	

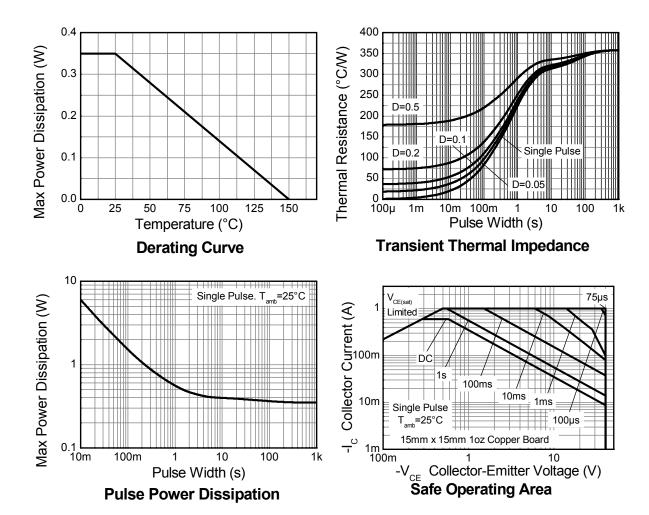
### ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air 7. Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.
  8. Thermal resistance from junction to solder-point (at the end of the leads).
  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics and Derating Information**





# Electrical Characteristics (@TA = +25°C unless otherwise specified)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	$BV_CBO$	60	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage(Note 10)	$BV_CEO$	40	1	V	$I_C = 10.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	1	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CEX</sub>		100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
Base Cutoff Current	$I_{BL}$		100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
ON CHARACTERISTICS (Note 10)					
DC Current Gain	h <sub>FE</sub>	20 40 80 100 40		_	$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 1.0 V \\ I_C &= 1.0 m A, \ V_{CE} = 1.0 V \\ I_C &= 10 m A, \ V_{CE} = 1.0 V \\ I_C &= 150 m A, \ V_{CE} = 1.0 V \\ I_C &= 500 m A, \ V_{CE} = 2.0 V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		0.40 0.75	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.75 —	0.95 1.2	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>cb</sub>		6.5	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>eb</sub>	_	30	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$
Input Impedance	h <sub>ie</sub>	1.0	15	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	8.0	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h <sub>fe</sub>	40	500	_	f = 1.0kHz
Output Admittance	h <sub>oe</sub>	1.0	30	μS	
Current Gain-Bandwidth Product	f⊤	250		MHz	$V_{CE} = 10V, I_{C} = 20mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>	_	15	ns	$V_{CC} = 30V, I_{C} = 150mA,$
Rise Time	tr	_	20	ns	$V_{BE(off)} = 2.0V, I_{B1} = 15mA$
Storage Time	ts	_	225	ns	$V_{CC} = 30V, I_{C} = 150mA,$
Fall Time	t <sub>f</sub>	_	30	ns	$I_{B1} = -I_{B2} = 15mA$

Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



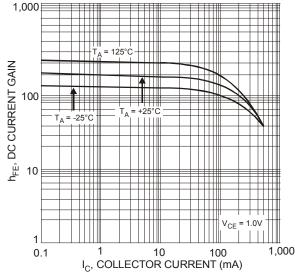
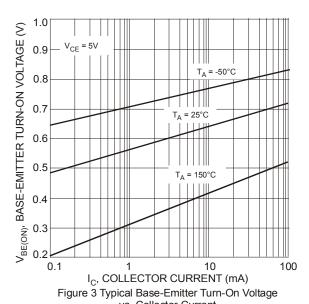


Figure 1 Typical DC Current Gain vs. Collector Current



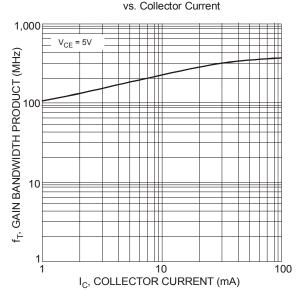


Figure 5 Typical Gain Bandwidth Product vs. Collector Current

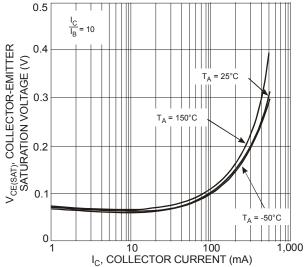


Figure 2 Collector-Emitter Saturation Voltage vs. Collector Current

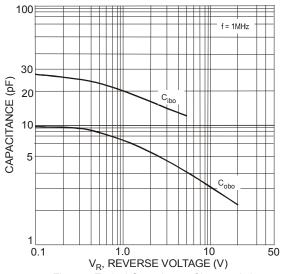


Figure 4 Typical Capacitance Characteristics

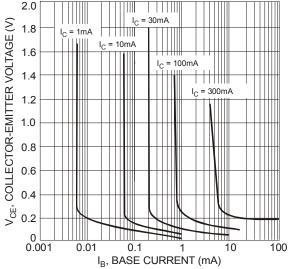
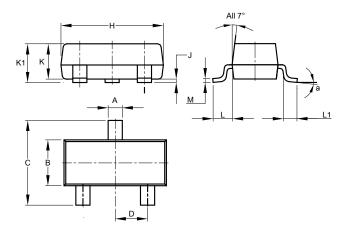


Figure 6 Typical Collector Saturation Region



### **Package Outline Dimensions**

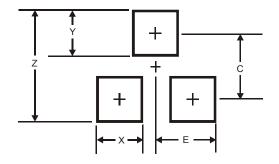
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Η	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	8°					
All	All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
С	2.0
Е	1.35



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